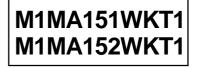




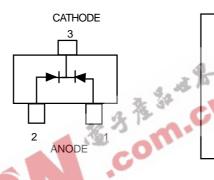
Common Anode Silicon Dual Switching diodes

These Common Cathode Silicon Epitaxial Planar Dual Diodes are designed for use in ultra high speed switching applications. These devices are housed in the SC-59 package which is designed for low power surface mount applications.

- Fast t _{rr} , < 3.0 ns
- Low C $_{\rm D}$, < 2.0 pF
- Available in 8 mm Tape and Reel Use M1MA151/2WKT1 to order the 7 inch/3000 unit reel. Use M1MA151/2WKT3 to order the 13 inch/10,000 unit reel.



SC-59 PACKAGE COMMON CATHODE DUAL SWITCHING DIODES 40/80 V-100mA SURFACE MOUNT



CASE 318D-03, STYLE3 SC-59

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating		Symbol	Value	Unit			
Reverse Voltage	M1MA151WAT1	V _R	40	Vdc			
	M1MA152WAT1		80				
Peak Reverse Voltage	M1MA151WAT1	V rm	40	Vdc			
	M1MA152WAT1		80				
Forward Current	Single	١ _F	100	mAdc			
	Dual		150				
Peak Forward Current	Single	I _{FM}	225	mAdc			
	Dual		340				
Peak Forward Surge Current	Single	I _{FSM} ⁽¹⁾	500	mAdc			
	Dual		750				
THERMAL CHARACTERISTICS							
Rating		Symbo	IMax	Unit			
Power Dissipation		PD	200	mW			
Junction Temperature		ΤJ	150	C			
Storage Temperature		T stg	-55 to +150	°C			

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

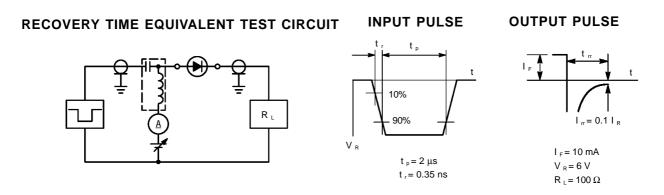
Characteristic		Symbol	Condition	Min	Max	Unit μAdc
Reverse Voltage Leakage Curre	e Current M1MA151WAT1		I_R $V_R = 35 V$	_	0.1	
	M1MA152WAT1		V _R = 75 V	_	0.1	
Forward Voltage		V F	I _F = 100 mA	—	1.2	Vdc
Reverse Breakdown Voltage	M1MA151WAT1	V _R	I _R = 100 μA	40	—	Vdc
	M1MA152WAT1			80	—	
Diode Capacitance		CD	$V_{R} = 0, f = 1.0 \text{ MHz}$	_	2.0	pF
Reverse Recovery Time		t rr (2)	$I_{F} = 10 \text{ mA}, V_{R} = 6.0 \text{ V},$	_	3.0	ns
			$R_{L} = 100\Omega, I_{rr} = 0.1 I_{R}$			

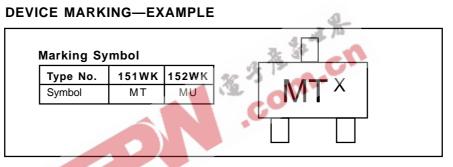
1. t = 1 SEC

2. t_{rr} Test Circuit



M1MA151WKT1 M1MA152WKT1





The "X" represents a smaller alpha digit Date Code. The Date Code indicates the actual month in which the part was manufactured.